

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Source-Source Voltage			V <sub>SSS</sub>	12	V
Gate-Source Voltage			V <sub>GSS</sub>	±8	V
Continuous Source Current (Note 5) V <sub>GS</sub> = 4.5V	Steady State	T <sub>A</sub> = +25°C	I <sub>S</sub>	23.6	A
		T <sub>A</sub> = +70°C		18.9	
Continuous Source Current (Note 5) V <sub>GS</sub> = 2.5V	Steady State	T <sub>A</sub> = +25°C	I <sub>S</sub>	16.8	A
		T <sub>A</sub> = +70°C		13.4	
Pulsed Source Current (Note 6)			I <sub>SM</sub>	100	A

**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 7)	P <sub>D</sub>	1.05	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 7)	R <sub>θJA</sub>	120.7	°C/W
Power Dissipation (Note 5)	P <sub>D</sub>	2.67	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 5)	R <sub>θJA</sub>	46.8	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Source-Source Breakdown Voltage	BV <sub>SSS</sub>	12	—	—	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1mA
Zero Gate Voltage Source Current T <sub>J</sub> = +25°C	I <sub>SSS</sub>	—	—	1	μA	V <sub>SS</sub> = 10V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±10	μA	V <sub>GS</sub> = ±8V, V <sub>SS</sub> = 0V
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.5	—	1.3	V	V <sub>SS</sub> = 6V, I <sub>S</sub> = 1mA
Static Source-Source On-Resistance	R <sub>SS(ON)</sub>	1.6	2.3	3.2	mΩ	V <sub>GS</sub> = 4.5V, I <sub>S</sub> = 5A
		1.7	2.4	3.2		V <sub>GS</sub> = 4.0V, I <sub>S</sub> = 5A
		1.8	2.5	3.2		V <sub>GS</sub> = 3.8V, I <sub>S</sub> = 5A
		1.9	2.7	4.4		V <sub>GS</sub> = 3.1V, I <sub>S</sub> = 5A
		2.1	3.0	6.3		V <sub>GS</sub> = 2.5V, I <sub>S</sub> = 5A
Diode Forward Voltage	V <sub>SS</sub>	—	0.7	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 3A
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	C <sub>iss</sub>	—	3315	—	pF	V <sub>SS</sub> = 6V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	850	—		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	248	—		
Total Gate Charge	Q <sub>g</sub>	—	56.5	—	nC	V <sub>SS</sub> = 6V, V <sub>GS</sub> = 4.5V, I <sub>S</sub> = 27A
Gate-Source Charge	Q <sub>gs</sub>	—	8.8	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	13.3	—		
Gate Charge at V <sub>TH</sub>	Q <sub>g(TH)</sub>	—	6.9	—		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	603	—	ns	V <sub>SS</sub> = 6V, V <sub>GS</sub> = 4.5V, I <sub>S</sub> = 3A
Turn-On Rise Time	t <sub>r</sub>	—	1694	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	4749	—		
Turn-Off Fall Time	t <sub>f</sub>	—	6208	—		

- Notes:
- Device mounted on FR-4 material with 1-inch<sup>2</sup> (6.45-cm<sup>2</sup>), 2-oz. (0.071-mm thick) Cu.
  - Repetitive rating, pulse width limited by junction temperature.
  - Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to production testing.

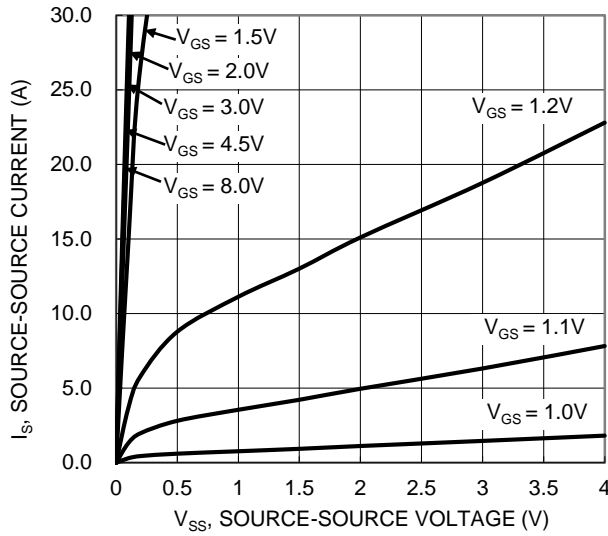


Figure 1. Typical Output Characteristic

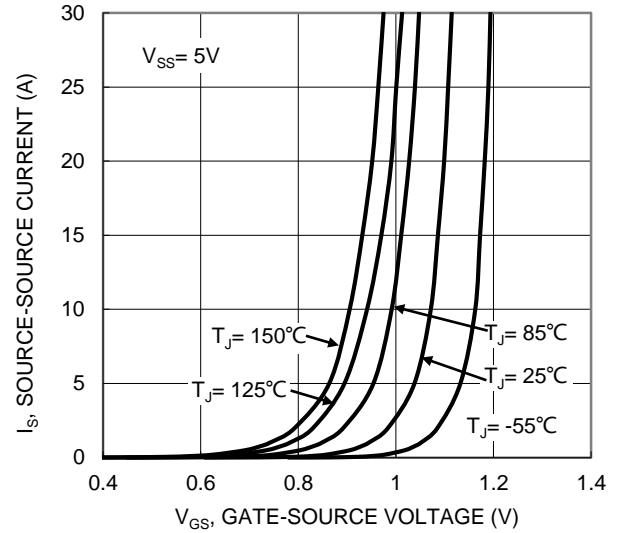


Figure 2. Typical Transfer Characteristic

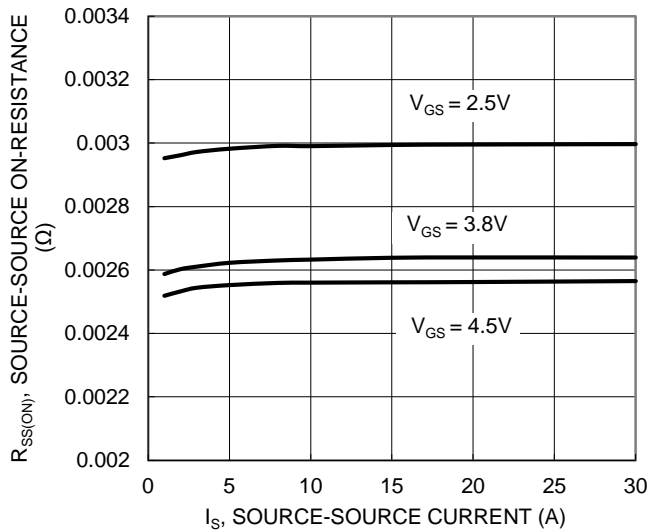


Figure 3. Typical On-Resistance vs. Source Current and Gate Voltage

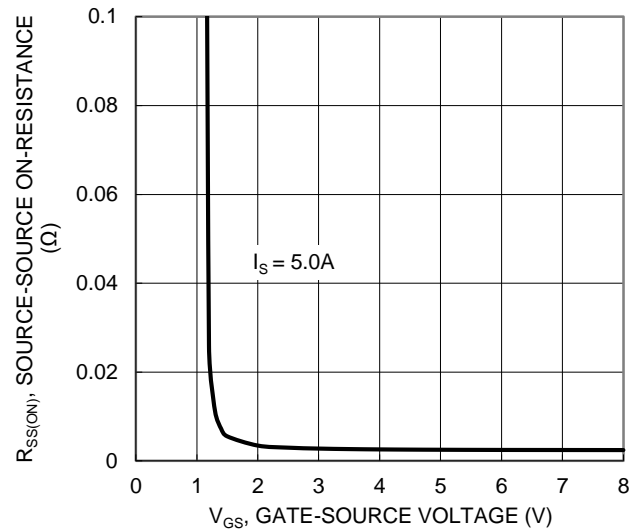


Figure 4. Typical Transfer Characteristic

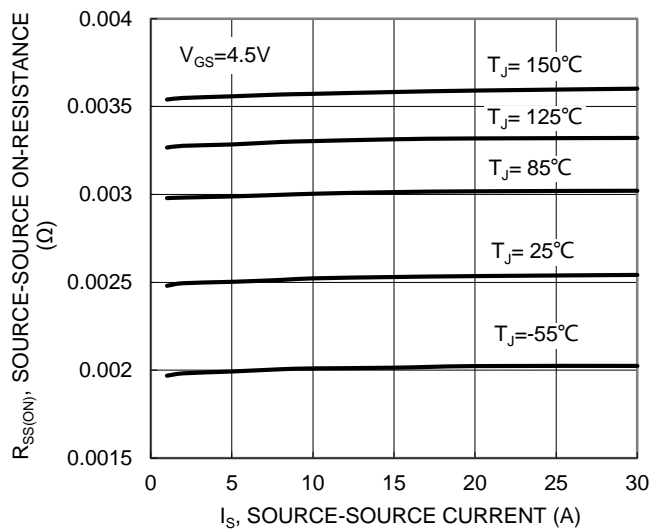


Figure 5. Typical On-Resistance vs. Source Current and Junction Temperature

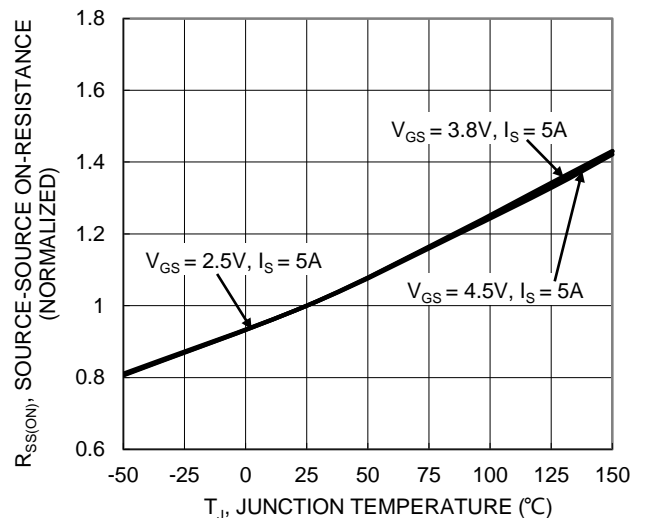


Figure 6. On-Resistance Variation with Junction Temperature

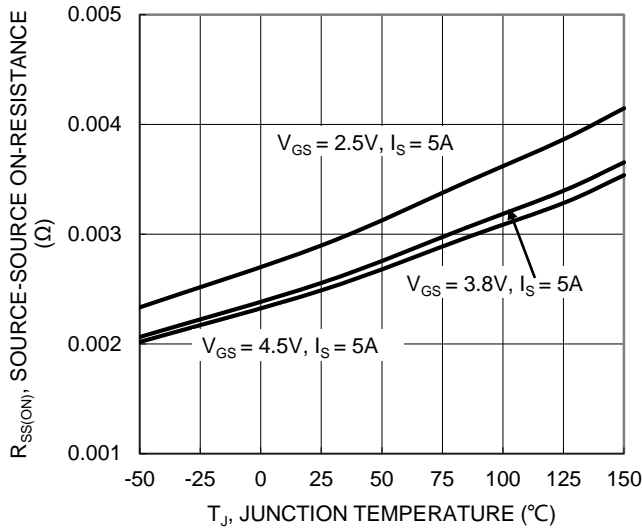


Figure 7. On-Resistance Variation with Junction Temperature

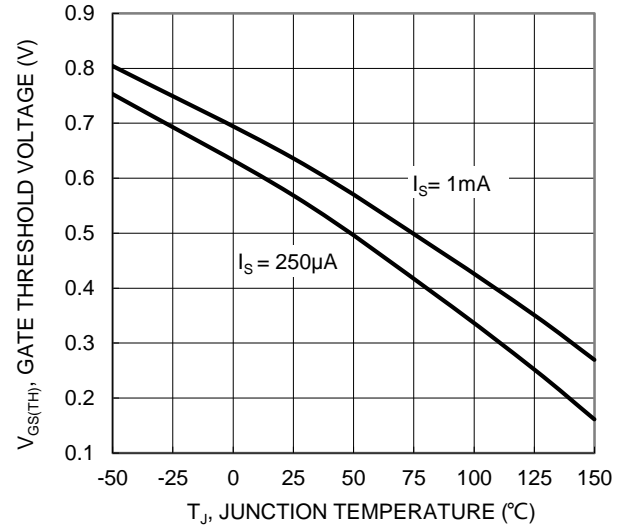


Figure 8. Gate Threshold Variation vs. Junction Temperature

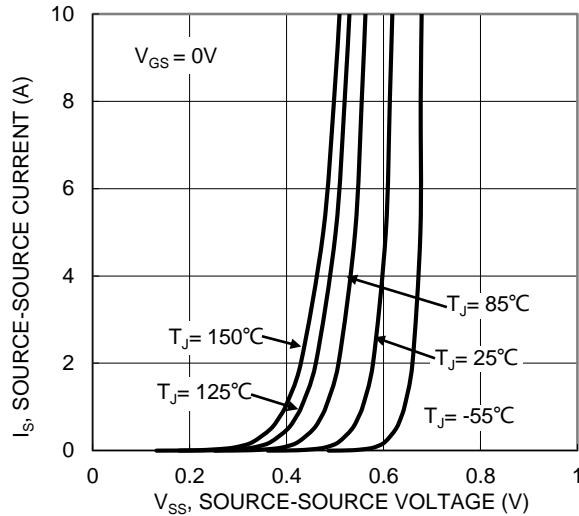


Figure 9. Diode Forward Voltage vs. Current

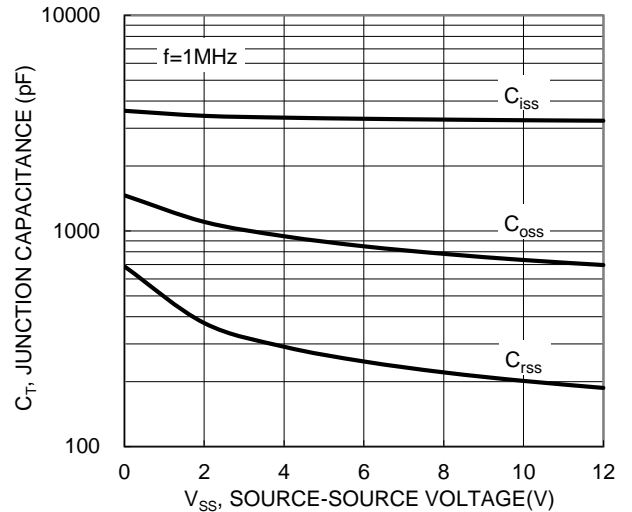


Figure 10. Typical Junction Capacitance

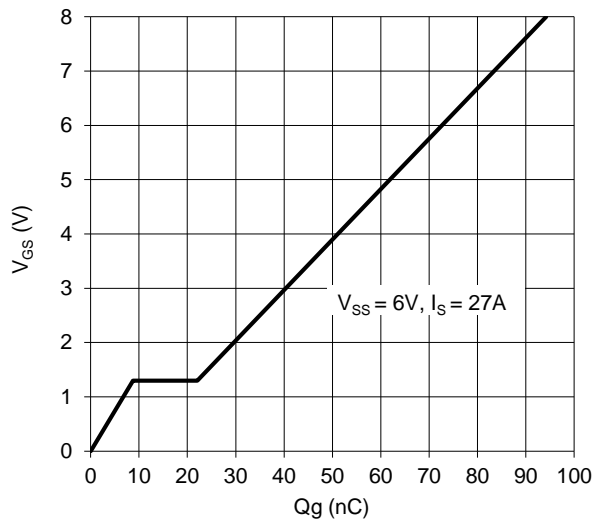


Figure 11. Gate Charge

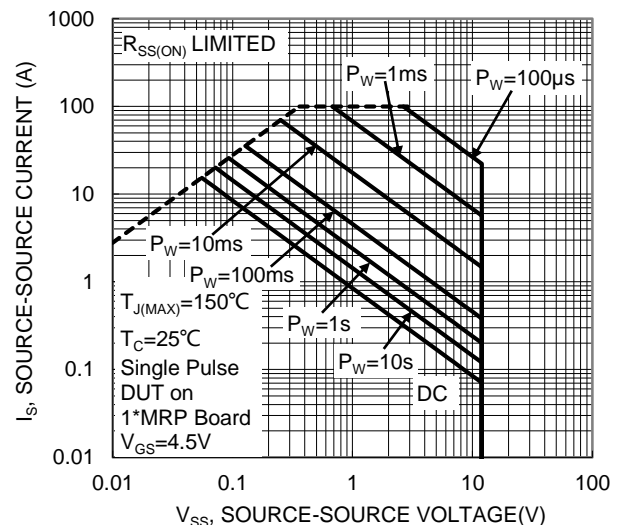


Figure 12. SOA, Safe Operation Area

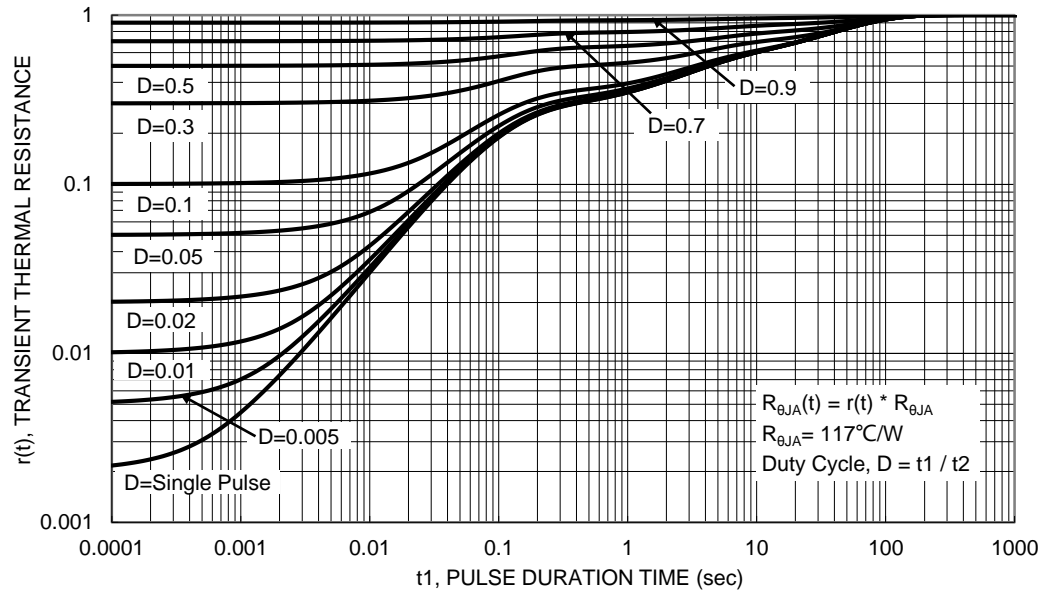
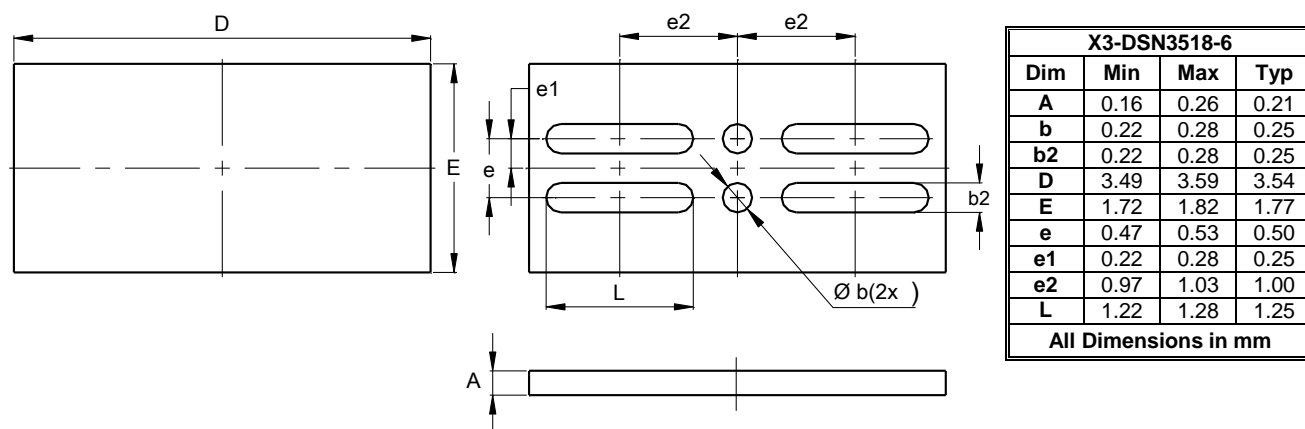


Figure 13. Transient Thermal Resistance

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

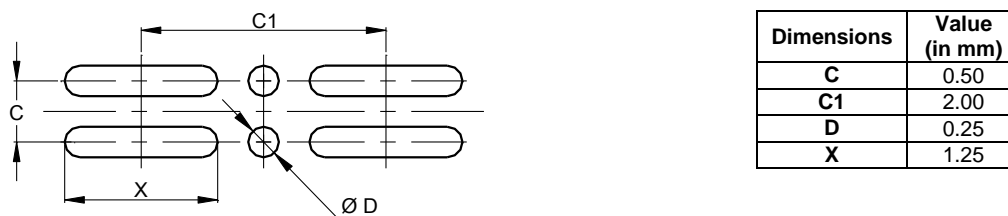
X3-DSN3518-6



## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

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